

CW Power Transistor, 14W 2.3 GHz

PH2323-14

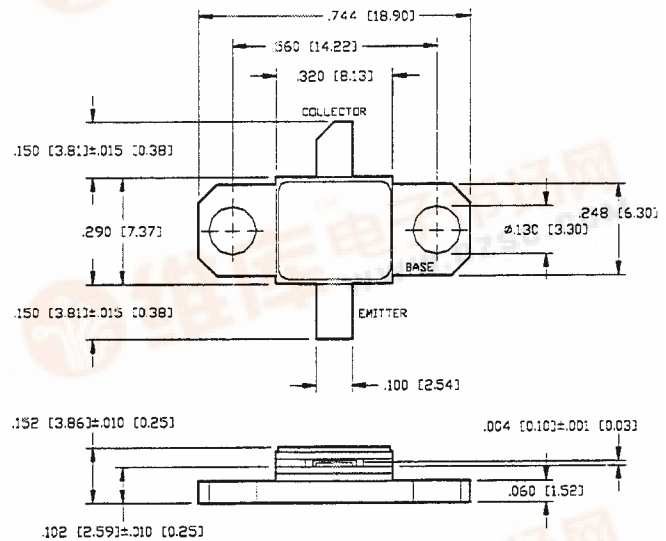
V2.00

Features

- NPN Silicon Microwave Power Transistor
- Common Base Configuration
- Class C Operation
- Interdigitated Geometry
- Gold Metalization System
- Hermetic Metal/Ceramic Package
- Diffused Emitter Ballasting Resistors
- Internal Input and Output Impedance Matching

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	60	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current	I_C	0.8	A
Power Dissipation	P_D	25	W
Junction Temperature	T_J	200	°C
Storage Temperature	T_{STG}	-65 to +200	°C
Thermal Resistance	θ_{JC}	4.5	°C/W



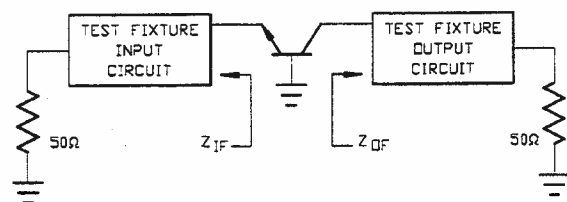
UNLESS OTHERWISE NOTED, TOLERANCES ARE
INCHES ±.005* (MILLIMETERS ±.13MM)

Electrical Characteristics at 25°C

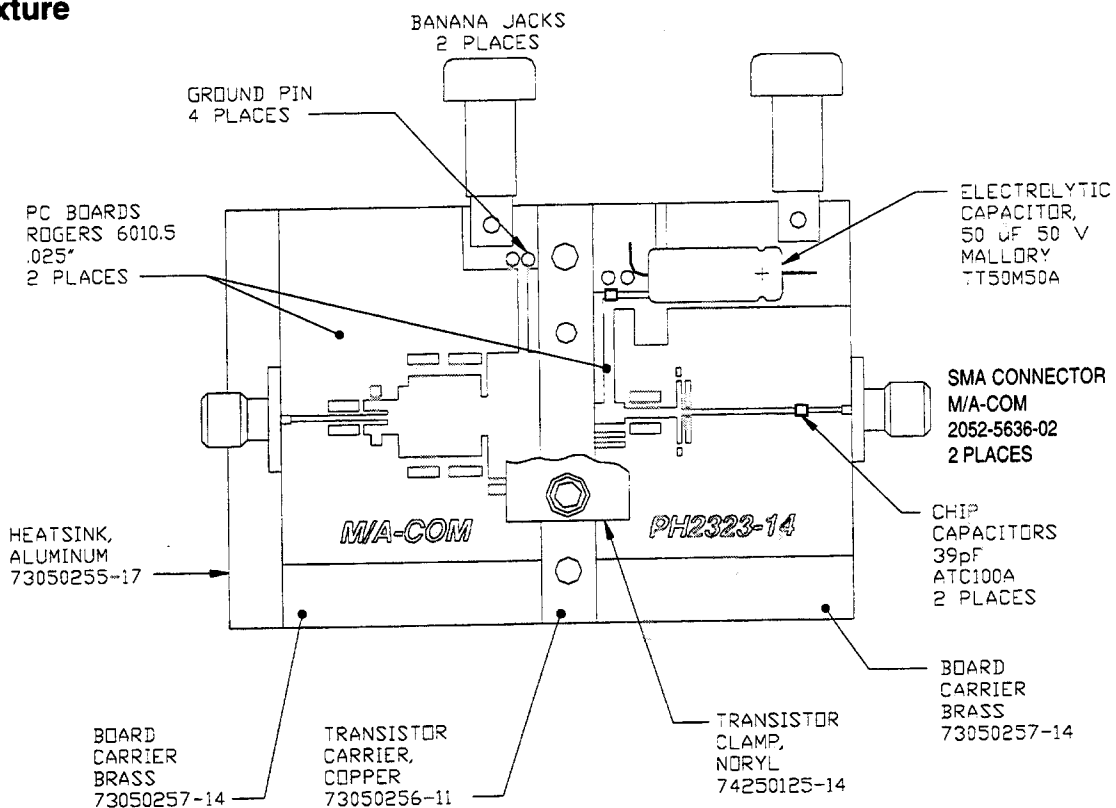
Parameter	Symbol	Min	Max	Units	Test Conditions
Collector-Emitter Breakdown Voltage	BV_{CES}	60	-	V	$I_C=10$ mA
Collector-Emitter Leakage Current	I_{CES}	-	2.0	mA	$V_{CE}=28$ V
Output Power	P_{OUT}	14	-	W	$V_{CC}=28$ V, $P_{IN}=2.5$ W, $F=2.3$ GHz
Power Gain	G_P	7.6	-	dB	$V_{CC}=28$ V, $P_{IN}=2.5$ W, $F=2.3$ GHz
Collector Efficiency	η_C	35	-	%	$V_{CC}=28$ V, $P_{IN}=2.5$ W, $F=2.3$ GHz
Input Return Loss	RL	10	-	dB	$V_{CC}=28$ V, $P_{IN}=2.5$ W, $F=2.3$ GHz
Load Mismatch Tolerance	VSWR-T	-	2:1	-	$V_{CC}=28$ V, $P_{IN}=2.5$ W, $F=2.3$ GHz

Test Fixture Impedances

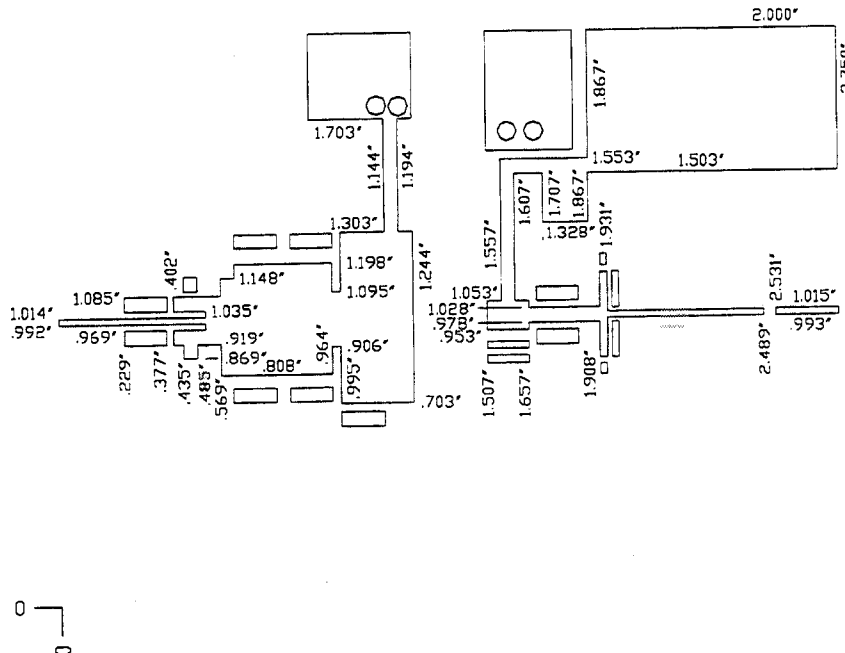
F(GHz)	$Z_{IF}(\Omega)$	$Z_{OF}(\Omega)$
2.30	$4.1 - j8.5$	$11.0 + j4.0$



RF Test Fixture



Test Fixture PC Board Dimensions



Specifications Subject to Change Without Notice.